

In the Claims

Claims 1-4 (Canceled).

5 (Original). An integrated circuit comprising:

a semiconductor structure;

a first trench formed of a first depth in said semiconductor structure; and

a second trench formed of a second depth crossing said first trench, deeper than said first depth, in said semiconductor structure and said second trench housing said second depth where said second trench crosses said first trench.

Claims 6-9 (Canceled).

10 (Original). An integrated circuit comprising:

a semiconductor structure;

a first trench formed of a first depth in said semiconductor structure;

a covering on said first trench and over said semiconductor structure, said covering being thicker in said first trench than over said semiconductor structure; and
said covering having an opening to define a region for a second trench.

11 (Original). The circuit of claim 10 wherein said covering is spin-on glass.

Claims 12-15 (Canceled).